

EH2525ETTTS-34.368M TR

Lead Free  COMPLIANT	EU RoHS 2011/65 + 2015/863 COMPLIANT	ChinaRoHS  COMPLIANT	REACH 163 SVHC COMPLIANT
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ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) HCMOS/TTL (CMOS) 5.0Vdc 4 Pad 5.0mm x 7.0mm Ceramic Surface Mount (SMD) 34.368MHz ± 25 ppm -40°C to +85°C

ELECTRICAL SPECIFICATIONS

Nominal Frequency	34.368MHz
Frequency Tolerance/Stability	± 25 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	± 5 ppm/year Maximum
Operating Temperature Range	-40°C to +85°C
Supply Voltage	5.0Vdc $\pm 10\%$
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOL= +16mA)
Rise/Fall Time	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	50 ± 5 (%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	± 250 pSec Maximum, ± 100 pSec Typical
One Sigma Clock Period Jitter	± 50 pSec Maximum, ± 30 pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-883, Method 2002, Condition B
Moisture Resistance	MIL-STD-883, Method 1004
Moisture Sensitivity	J-STD-020, MSL 1
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

EH2525ETTTS-34.368M TR

MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	34.368M
3	XXXXX XXXXX=Ecliptek Manufacturing Identifier

Suggested Solder Pad Layout

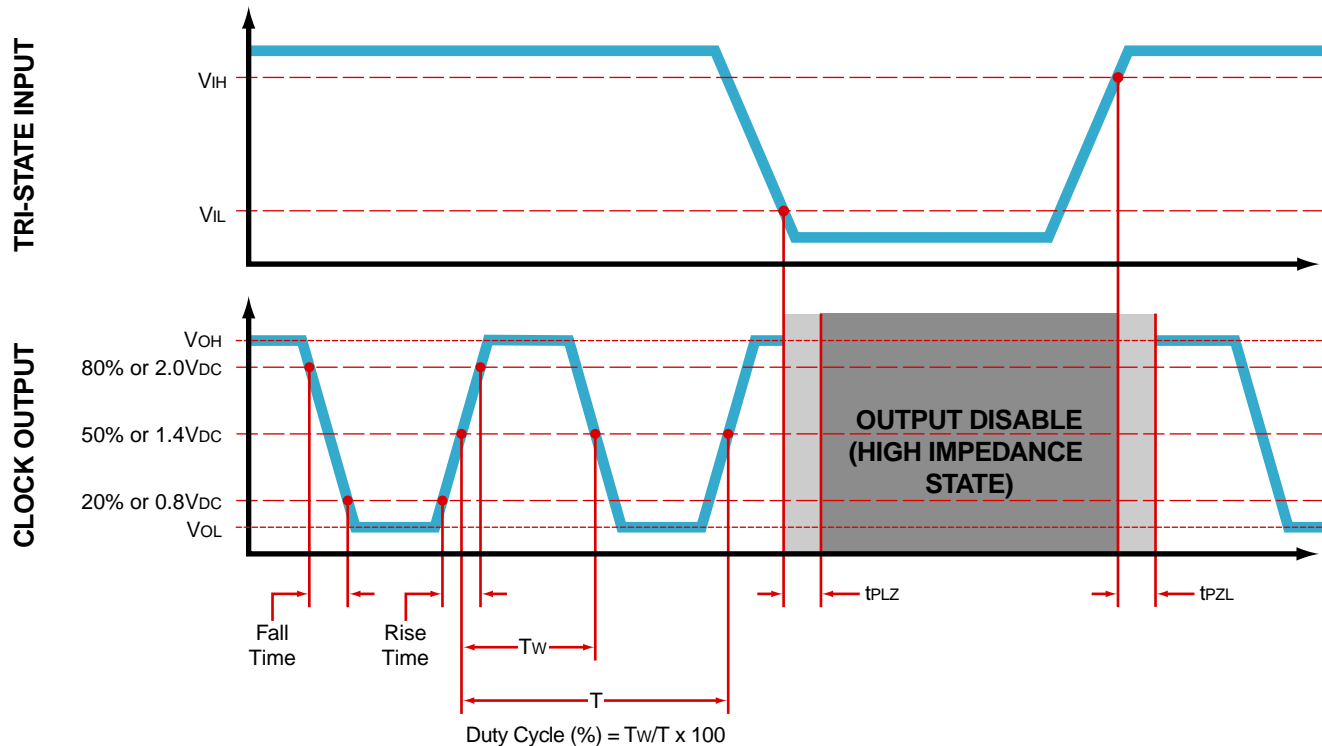
All Dimensions in Millimeters



All Tolerances are ±0.1

EH2525ETTTS-34.368M TR

OUTPUT WAVEFORM & TIMING DIAGRAM

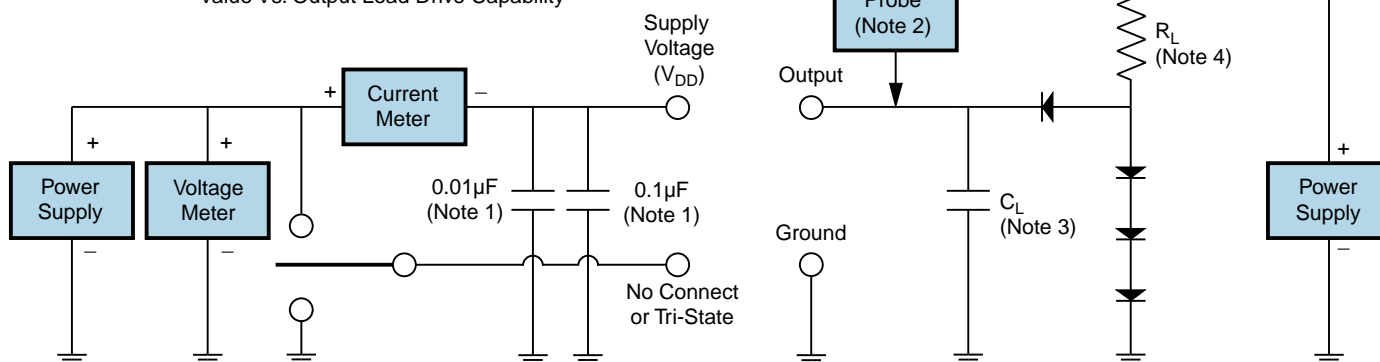


EH2525ETTTS-34.368M TR

Test Circuit for TTL Output

Output Load Drive Capability	R_L Value (Ohms)	C_L Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability



Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

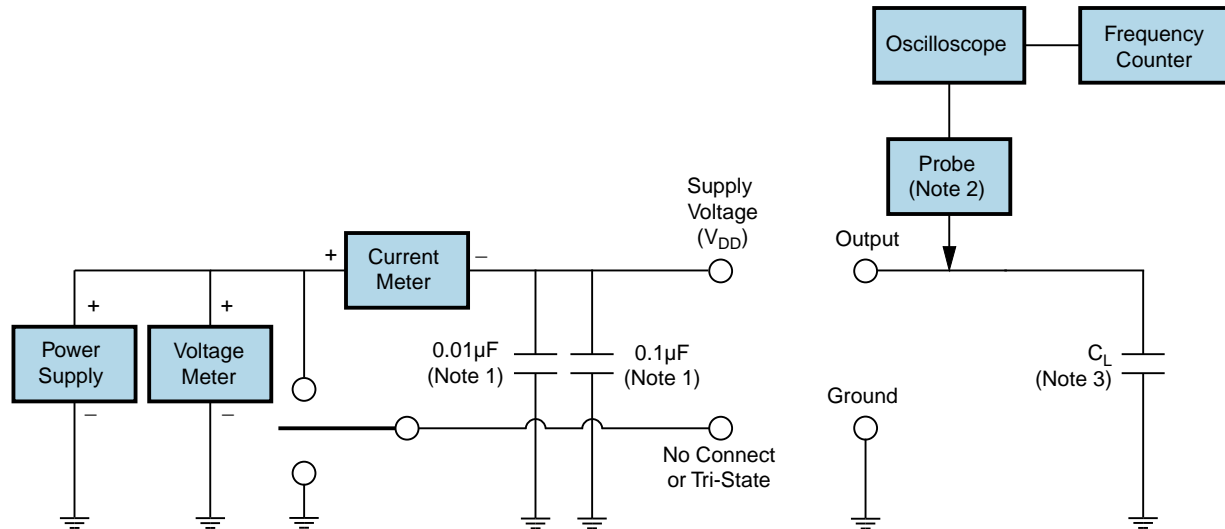
Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

EH2525ETTTS-34.368M TR

Test Circuit for CMOS Output



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Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

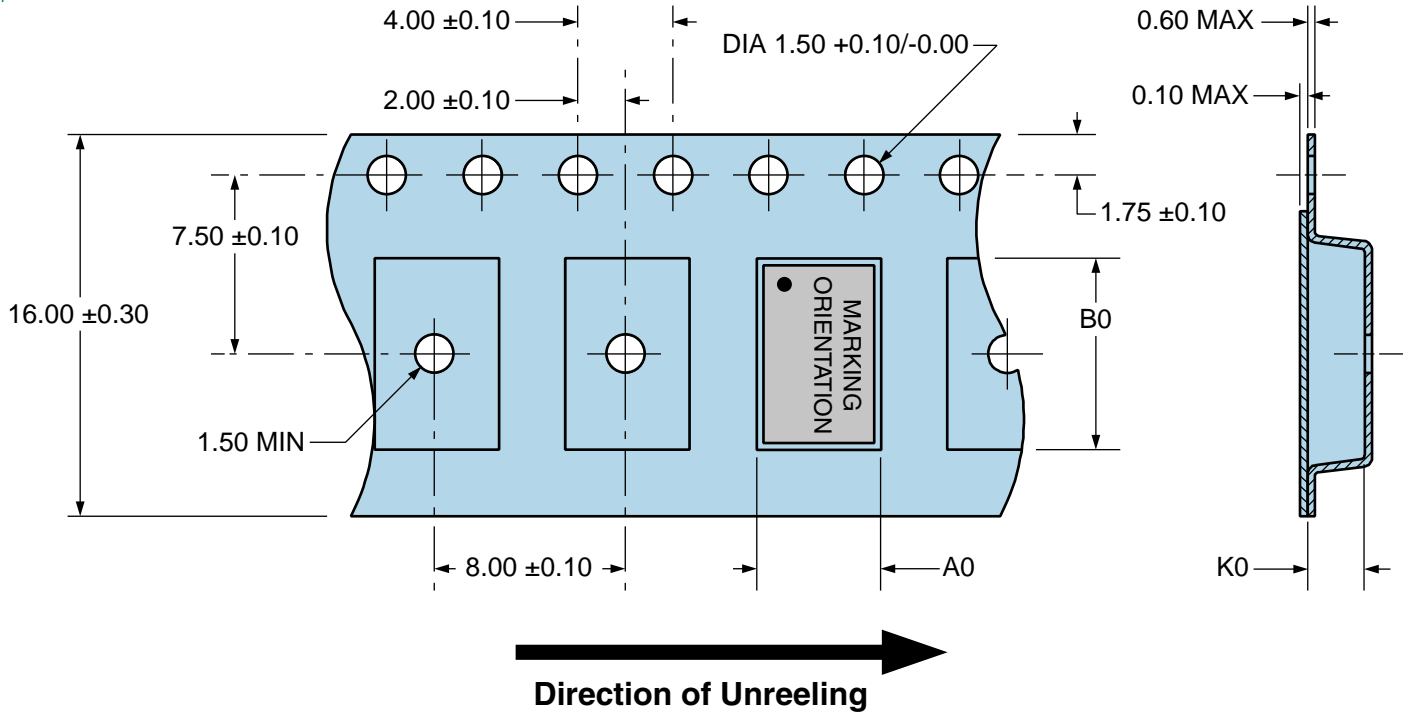
EH2525ETTTS-34.368M TR

Tape & Reel Dimensions

Quantity Per Reel: 1,000 units

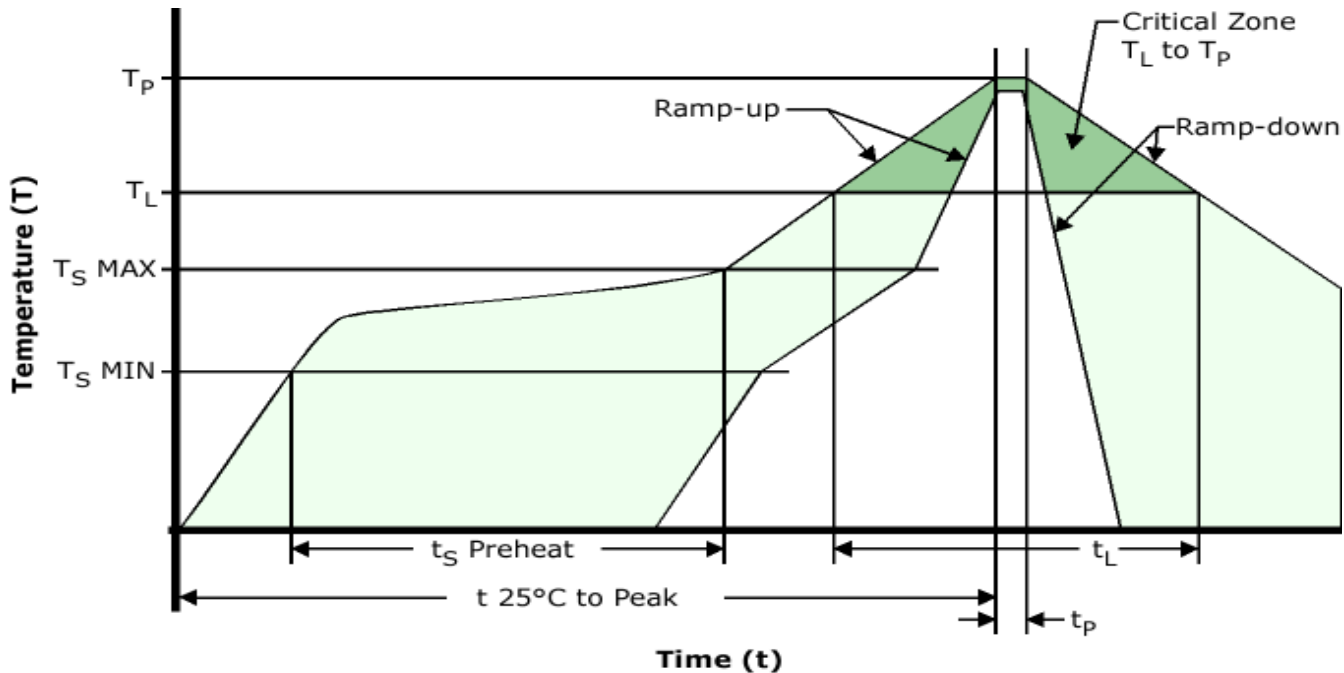
All Dimensions in Millimeters

Compliant to EIA-481



EH2525ETTTS-34.368M TR [↗](#)

Recommended Solder Reflow Methods

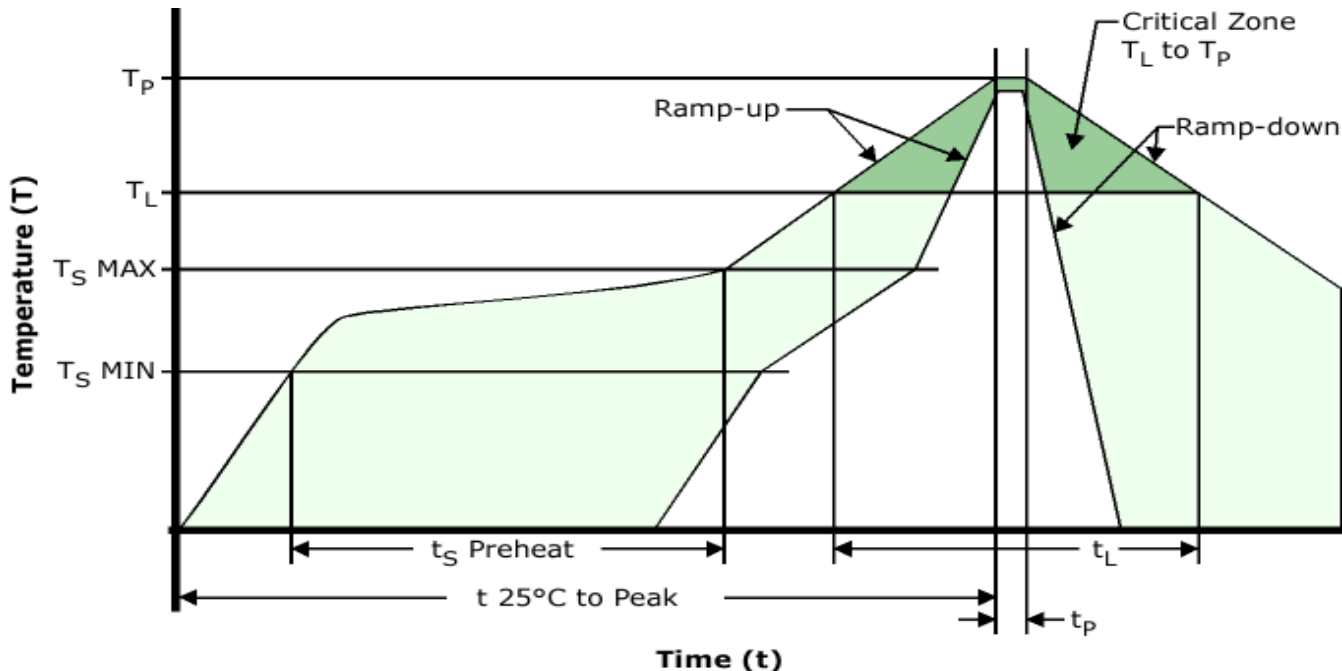


High Temperature Infrared/Convection

Ts MAX to TL (Ramp-up Rate)	3°C/Second Maximum
Preheat	
- Temperature Minimum (Ts MIN)	150°C
- Temperature Typical (Ts TYP)	175°C
- Temperature Maximum (Ts MAX)	200°C
- Time (ts MIN)	60 - 180 Seconds
Ramp-up Rate (TL to TP)	3°C/Second Maximum
Time Maintained Above:	
- Temperature (TL)	217°C
- Time (tL)	60 - 150 Seconds
Peak Temperature (TP)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (TP Target)	250°C +0/-5°C
Time within 5°C of actual peak (tp)	20 - 40 Seconds
Ramp-down Rate	6°C/Second Maximum
Time 25°C to Peak Temperature (t)	8 Minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

EH2525ETTTS-34.368M TR [↗](#)

Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

Ts MAX to TL (Ramp-up Rate) 5°C/Second Maximum

Preheat

- Temperature Minimum (Ts MIN) N/A
 - Temperature Typical (Ts TYP) 150°C
 - Temperature Maximum (Ts MAX) N/A
 - Time (ts MIN) 60 - 120 Seconds

Ramp-up Rate (TL to TP) 5°C/Second Maximum

Time Maintained Above:

- Temperature (TL) 150°C
 - Time (tL) 200 Seconds Maximum

Peak Temperature (TP) 240°C Maximum

Target Peak Temperature (TP Target) 240°C Maximum 2 Times / 230°C Maximum 1 Time

Time within 5°C of actual peak (tp) 10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time

Ramp-down Rate 5°C/Second Maximum

Time 25°C to Peak Temperature (t) N/A

Moisture Sensitivity Level Level 1

Additional Notes Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)